To electrically detect the ISHE, we fabricated H-shaped mesa structures (Fig. 1) using electron beam lithography and dry-etching techniques, following a design proposed previously by some of us [16]. A Au/Ti electrode was deposited on top of a 110-nm-thick SiO/SiN gate insulator layer that covered the entire sample. Ohmic contacts were fabricated by thermal In bonding. Two additional leads were added to the H-structures to allow further characterization measurements. They were attached to a vertical leg either far away from (for example, sample 2197, Fig. 1a) or in close proximity to the horizontal leg of the H-bar (for example, sample 2198, Fig. 1b). The H-structures consisted of legs 1 µm long and 200 nm wide, with the connecting part being 200 nm wide and 200 nm long. With a mean free path estimated at $l \geq 2.5 \mu m$, the samples studied were well within the quasi-ballistic regime.